

Claim Status

Claims 1-13 (Cancelled)

5 14. (Original) A method for forming an emitter, comprising the steps of:
 forming a patterned oxide layer to define an emission area upon an
 electron supply layer; and
 forming a quantum dot zeolite emission layer comprising a plurality of
 cages and having semiconductor materials held within said cages.

10 15. (Original) The method of claim 14, further comprising a step of forming a metal
 contact structure on the pattered oxide layer.

15 16. (Original) The method of claim 15, further comprising a step of forming a thin
 metal layer on the quantum dot zeolite emission layer and the metal contact
 structure.

20 17. (Original) The method of claim 15, wherein the metal contact structure
 comprises a single metal layer.

25 18. (Original) The method of claim 15, wherein the metal contact structure
 comprises multiple metal layers.

20 19. (Original) The method of claim 14, wherein said step of forming an quantum
 dot zeolite emission layer comprises forming a zeolite layer having a thickness in
 the approximate range of 0.05 – 0.5 micrometers.

30 20. (Original) The method of claim 14, performed as part of an integrated circuit
 formation process to form the emitter as part of an integrated circuit including
 emitter control circuitry.

Claims 21-35 (Cancelled)